

DCG010

Silicon Epitaxial Planar Type (Cathode Common)

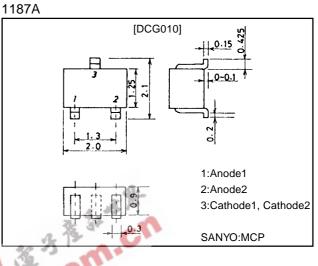
Ultrahigh-Speed Switching Diode

Features

- · Ideally suited for use in hybrid ICs because of very small-sized package.
- · Fast switching speed.
- · Small interterminal capacitance.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

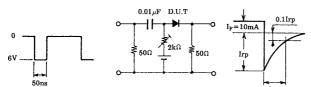
| Parameter | | Symbol | | Conditions | Ratings | Unit |
|-----------------------------|--|-----------------|--------------|------------|-------------|------|
| Peak Reverse Voltage | | V _{RM} | | | 85 | V |
| Reverse Voltage | | VR | | | 80 | V |
| Peak Forward Current | | IFM | Unit rating | | 300 | mA |
| | | | Total rating | | 450 | mA |
| Average Rectified Current | | lo | Unit rating | | 100 | mA |
| | | | Total rating | | 150 | mA |
| Surge Current(1µs) | | FSM | Unit rating | | 4 | А |
| | | | total rating | | 6 | А |
| Allowable Power Dissipation | | Р | | | 100 | mW |
| Junction Temperature | | Tj | | | 125 | °C |
| Storage Temperature | | Tstg | | | -55 to +150 | °C |

Electrical Characteristics at Ta = 25°C

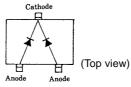
| Parameter | Symbol | Conditions | Ratings | | | Unit |
|---------------------------|-----------------|--|---------|------|------|------|
| i alameter | | | min | typ | max | Unit |
| Forward Voltage | V _{F1} | I _F =1mA | | 0.60 | | V |
| | V _{F2} | I _F =10mA | | 0.72 | | V |
| | V _{F3} | I _F =100mA | | | 1.20 | V |
| Reverse Current | I _{R1} | V _R =30V | | | 0.1 | μA |
| | I _{R2} | V _R =80V | | | 0.5 | μA |
| Interterminal Capacitance | С | V _R =0V, f=1MHz | | | 3.0 | pF |
| Reverse Recovery Time | trr | I _F =10mA, V _R =6V, R _L =50Ω, I _{rr} =0.1Irp | | | 4.0 | ns |

Marking:W6

Reverse Recovery Time Test Circuit

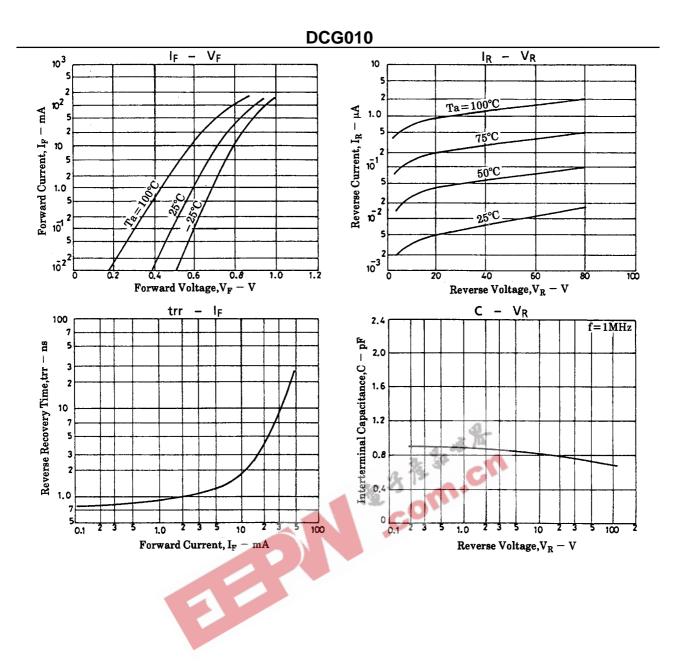


Electrical Connection



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